

WHAT IS CLAIMED IS:

1. A group III nitride compound semiconductor light-emitting device, comprising:

a semiconductor laminate portion including a  
5 light-emitting layer; and

a reflection surface disposed so as to be opposite to a side surface of said semiconductor laminate portion, wherein said semiconductor laminate portion and said reflection surface are provided in one and the same chip.

2. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface reflects light from said side surface of said semiconductor laminate portion into a direction of an optical axis of said light-emitting device.

3. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a distance between said reflection surface and said side surface of said semiconductor laminate portion is in a range of from 0.1 to 10  $\mu\text{m}$ .

4. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface is made of a material which is the same as

that of an n pad electrode .

5. A group III nitride compound semiconductor light-emitting device according to claim 4, wherein a portion  
5 of said n pad electrode opposite to said side surface of said semiconductor laminate portion forms a second reflection surface.

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10 6. A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed on an n-type semiconductor layer which is formed by etching to be a first depth, and said n pad electrode is formed on said n-type semiconductor layer which is formed by etching to be a second depth shallower than said  
15 first depth.

7. A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed integrally with said n pad  
20 electrode .

8. A group III nitride compound semiconductor light-emitting device, comprising:  
a laminate of group III nitride compound semiconductor  
25 layers inclusive of a light-emitting layer;

a groove formed in said laminate; and  
a reflection surface formed on an outer side surface of  
said groove.

5           9.     A group III nitride compound semiconductor  
light-emitting device according to claim 8, wherein said groove  
is formed by a dicing saw.

10           10.    A group III nitride compound semiconductor  
light-emitting device according to claim 8, wherein said  
reflection surface is made of a metal layer.

15           11.    A group III nitride compound semiconductor  
light-emitting device according to claim 10, wherein said metal  
layer is made of a material which is the same as that of an  
n pad electrode , and said metal layer is formed at the same  
time when said n pad electrode is formed.

20           12.    A group III nitride compound semiconductor  
light-emitting device according to claim 8, wherein light  
emitted from a side surface of said laminate is reflected by  
said reflected surface in a direction of an optical axis of  
said light-emitting device.

25           13.    A group III nitride compound semiconductor

light-emitting device according to claim 8, wherein said groove has a depth to reach a substrate.

14. A group III nitride compound semiconductor  
5 light-emitting device according to claim 8, wherein said groove is substantially parallel to a chip cutting line.

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